

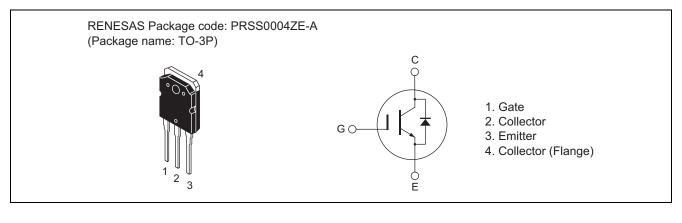
RJH60F0DPK

Silicon N Channel IGBT High Speed Power Switching

Features

- High speed switching
- Low on-state voltage
- Fast recovery diode

Outline



Absolute Maximum Ratings

(Tc = 25°C)

				$(10 - 20 \ 0)$
	Item	Symbol	Ratings	Unit
Collector to emitter volt	age	V _{CES}	600	V
Gate to emitter voltage		V _{GES}	±30	V
Collector current	Tc = 25 °C	I _C Note1	50	A
	Tc = 100°C	I _C Note1	25	A
Collector peak current		ic(peak) ^{Note1}	100	A
Collector to emitter dio	de forward peak current	i _{DF} (peak) ^{Note2}	100	А
Collector dissipation		P _C ^{Note3}	201.6	W
Channel temperature		Tj	150	°C
Storage temperature		Tstg	–55 to +150	°C

Notes: 1. Pulse width limited by safe operating area.

2. $PW \leq 5~\mu s,~duty~cycle \leq 1\%$

3. Value at Tc = 25°C

Electrical Characteristics

						(Tj = 25°C)
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Zero gate voltage collector current	I _{CES}	_	—	100	μA	V _{CE} = 600V, V _{GE} = 0
Gate to emitter leak current	I _{GES}	_	—	±1	μA	$V_{GE} = \pm 30 \text{ V}, \text{ V}_{CE} = 0$
Gate to emitter cutoff voltage	V _{GE(off)}	4	—	8	V	V _{CE} = 10V, I _C = 1 mA
Collector to emitter saturation voltage	V _{CE(sat)}	_	1.4	1.82	V	I _C = 25 A, V _{GE} = 15V ^{Note4}
		_	1.7	_	V	I_{C} = 50 A, V_{GE} = 15V ^{Note4}
Switching time	tr	_	90	_	ns	$I_{C} = 30 \text{ A, Resistive Load}$ $V_{CC} = 300 \text{ V}$ $V_{GE} = 15 \text{ V}$ $Rg = 5 \Omega$ ^{Note4}
C-E diode forward voltage	V _{ECF1}	_	1.6	2.1	V	I _F = 20 A ^{Note4}
C-E diode forward voltage	V _{ECF2}	_	1.8	_	V	$I_F = 40 \text{ A}^{\text{Note4}}$
C-E diode reverse recovery time	t _{rr}	_	140	—	ns	I _F = 20 A di _F /dt = 100 A/μs

Notes: 4. Pulse test

Package Dimensions

Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]	
Package Name TO-3P	SC-65	PRSS0004ZE-A	TO-3P / TO-3PV	5.0g	1.1
	<u>1.6</u>	15.6 ± 0.3	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$		2
	<u>5.45 ± 0</u>		<u>.0</u> <u>.0</u> <u></u> <u>5.45 ± 0.5</u>		

Ordering Information

Part No.	Quantity	Shipping Container
RJH60F0DPK-00-T0	360 pcs	Box (Tube)

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